

CORRECTION in EC201/EC101

ELECTRONICS ENGG

Morning Shift: May 22, 2015

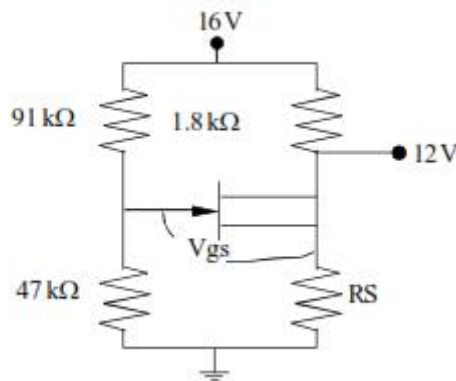
**For EC201 students (ONLY FOR MTU NOIDA CARRY OVER STUDENTS)
question 5 of EEC201/EC201 should be replaced by following question:**

5. Attempt any **two** parts of the following:

(10×2=20)

(a) Define and explain the given parameter transconductance (g_m), drain resistance (r) and amplification (μ) of a JFET. In JFET $I_{DSS} = 8 \text{ mA}$, $V_P = -4 \text{ V}$ biased at $V_{GS} = -1.8 \text{ V}$. Determine the value g_m .

(b) For voltage divider configuration of figure, if $V_D = 12 \text{ V}$ and $V_{GSQ} = -2 \text{ V}$, determine the value of resistance (R_S).



(c) Explain enhancement type MOSFET with diagram and draw the transfer and output characteristics.